

August 2014

### FQPF5P20

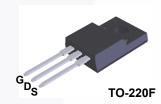
# P-Channel QFET<sup>®</sup> MOSFET -200 V, -3.4 A, 1.4 $\Omega$

### Description

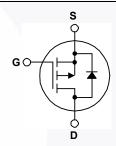
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- -3.4 A, -200 V,  $R_{DS(on)}$  = 1.4  $\Omega$  (Max.) @  $V_{GS}$  = -10 V,  $I_D$  = -1.7 A
- Low Gate Charge (Typ. 10 nC)
- Low C<sub>rss</sub> (Typ. 12 pF)
- · 100% Avalanche Tested







### **Absolute Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF5P20 FQPF5P20RDTU	Unit
$V_{DSS}$	Drain-Source Voltage		-200	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-3.4	Α
	- Continuous (T <sub>C</sub> = 100°C)		-2.15	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-13.6	Α
$V_{GSS}$	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	330	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-3.4	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	3.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		38	W
	- Derate Above 25°C		0.3	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQPF5P20 FQPF5P20RDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max. 3.29		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max. 62.5		C/VV

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF5P20	FQPF5P20	TO-220F	Tube	N/A	N/A	50 units
FQPF5P20RDTU	FQPF5P20	TO-220F (LG-formed)	Tube	N/A	N/A	50 units

### **Elerical Characteristics** $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-200			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 μA, Referenced to 25°C		-0.17		V/°C
I <sub>DSS</sub>	Zana Cata Valtana Duain Cumant	V <sub>DS</sub> = -200 V, V <sub>GS</sub> = 0 V	-		-1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -160 V, T <sub>C</sub> = 125°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.7 A		1.1	1.4	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -40 V, I <sub>D</sub> = -1.7 A		2.15		S
	ic Characteristics		T			
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		330	430	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		75	98	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			12	15	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -100 \text{ V}, I_D = -4.8 \text{ A},$		9	28	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$	/	70	150	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	5 32		12	35	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	25	60	ns
Qg	Total Cata Charge	V <sub>DS</sub> = -160 V, I <sub>D</sub> = -4.8 A,		10	13	
9	Total Gate Charge	VDS = -100 V, ID = -4.0 A,				nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{\text{DS}} = -100 \text{ V}, I_{\text{D}} = -4.8 \text{ A},$ $V_{\text{GS}} = -10 \text{ V}$		2.8		nC nC

### **Drain-Source Diode Characteristics and Maximum Ratings**

		•				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-3.4	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	-		-13.6	Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -3.4 A			-5.0	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V, I}_{S} = -4.8 \text{ A,}$	-	175		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$	-	1.07		μС

- **Notes:**1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 42.8 mH,  $I_{AS}$  = -3.4 A,  $V_{DD}$  = -50 V,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25°C. 3.  $I_{SD}$  ≤ -4.8 A, di/dt ≤ 300 A/µs,  $V_{DD}$  ≤ BV $_{DSS}$ , starting  $T_J$  = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

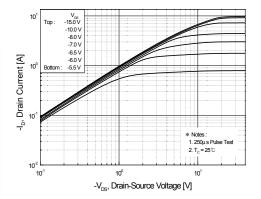


Figure 1. On-Region Characteristics

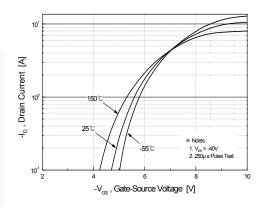


Figure 2. Transfer Characteristics

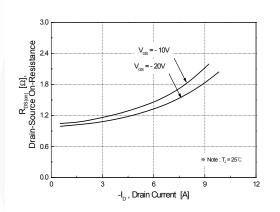


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

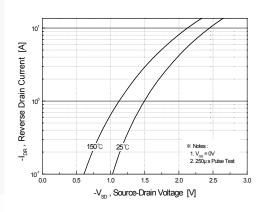


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

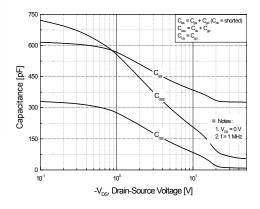


Figure 5. Capacitance Characteristics

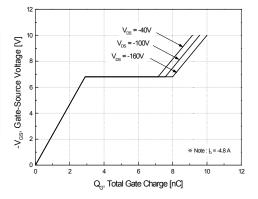
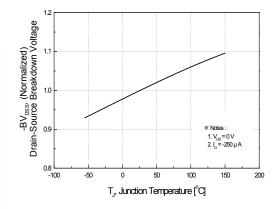


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)



R<sub>DS(ON)</sub>, (Normalized) Drain-Source On-Resistance 1.0 0.0 L -100 150 200

Figure 7. Breakdown Voltage Variation vs. Temperature

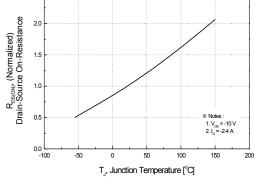
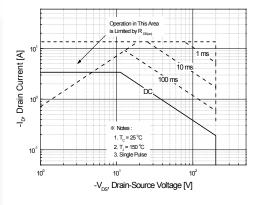


Figure 8. On-Resistance Variation vs. Temperature



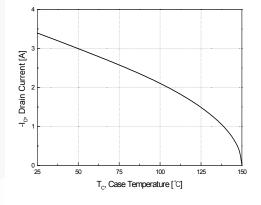


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

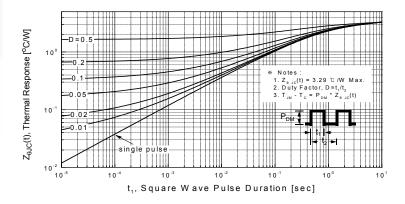


Figure 11. Transient Thermal Response Curve

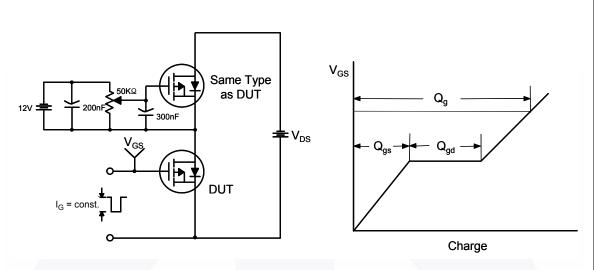


Figure 12. Gate Charge Test Circuit & Waveform

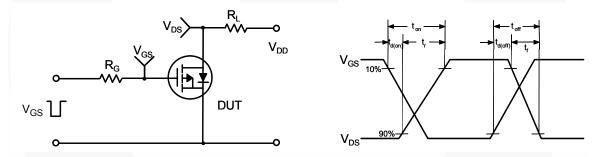


Figure 13. Resistive Switching Test Circuit & Waveforms

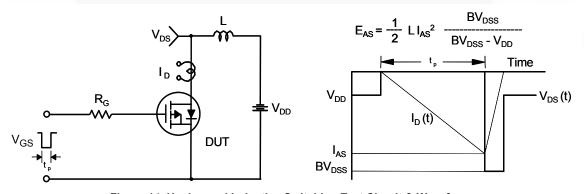
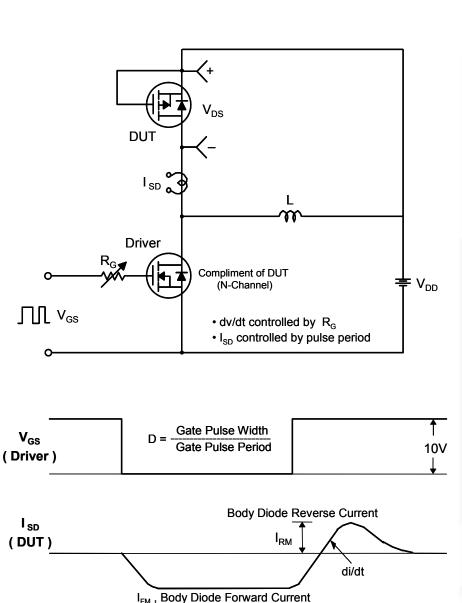


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

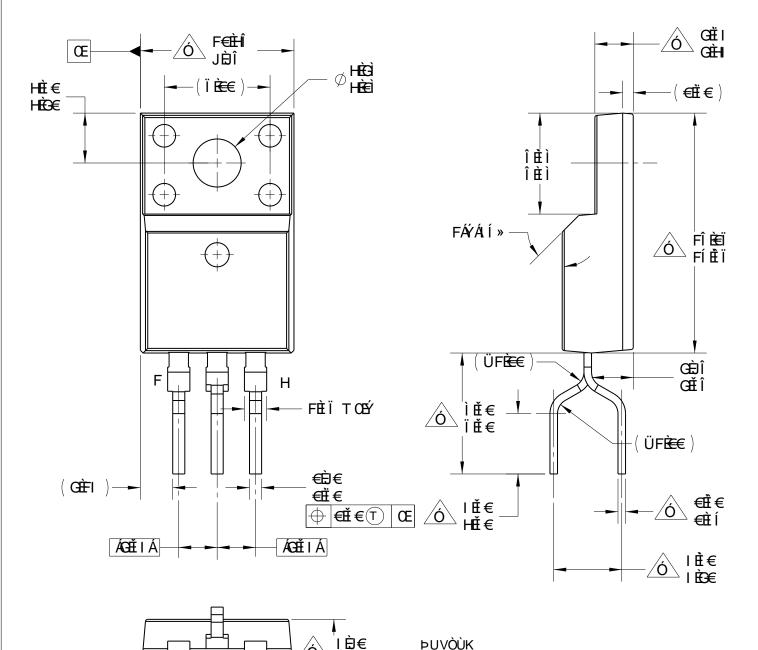


V<sub>DS</sub>
(DUT)

Body Diode
Forward Voltage Drop
Body Diode Recovery dv/dt

Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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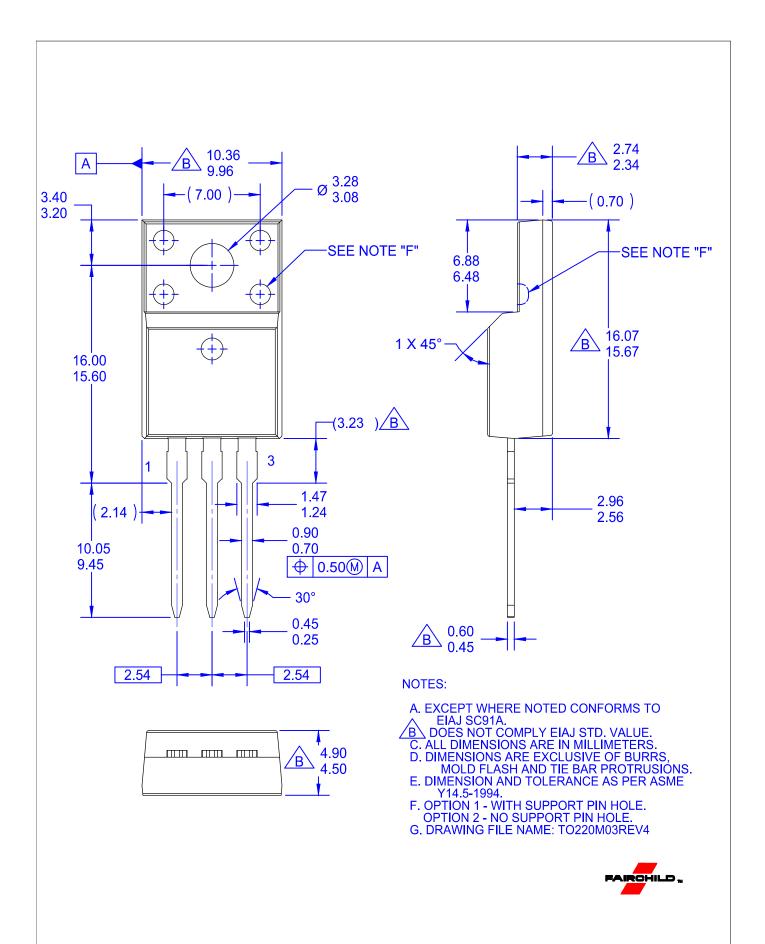
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